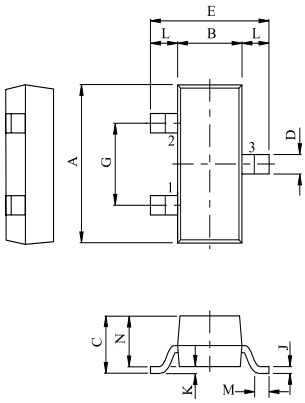
2N3904SC

EPITAXIAL PLANAR NPN TRANSISTOR

GENERAL PURPOSE APPLICATION.
SWITCHING APPLICATION.

FEATURES

- Low Leakage Current
  : I_{CEX}=50nA(Max.), I_{BL}=50nA(Max.)
  @V_{CE}=30V, V_{EB}=3V.
- Excellent DC Current Gain Linearity.
- Low Saturation Voltage
  : $V_{CE(sat)}$=0.3V(Max.) @I_C=50mA, I_B=5mA.
- Complementary to 2N3906SC.



DIM	MILLIMETERS
A	2.90±0.1
B	1.30+0.20/-0.15
C	1.30 MAX
D	0.40+0.15/-0.05
E	2.40+0.30/-0.20
G	1.90
J	0.10
K	0.00 ~ 0.10
L	0.55
M	0.20 MIN
N	1.00+0.20/-0.10

1. EMITTER
2. BASE
3. COLLECTOR

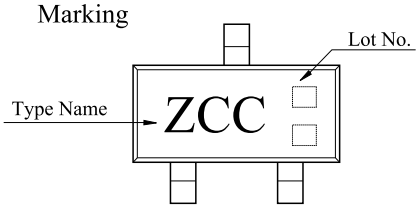
SOT-23(1)

MAXIMUM RATING (Ta=25℃)

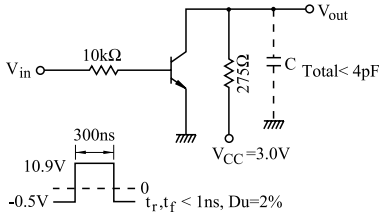
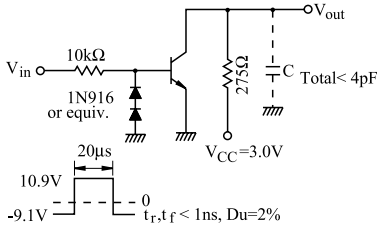
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	200	mA
Base Current	I_B	50	mA
Collector Power Dissipation	P_C *	350	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 150	℃

* PC : Package Mounted On 99.5% Alumina 10×8×0.6㎜)

Marking

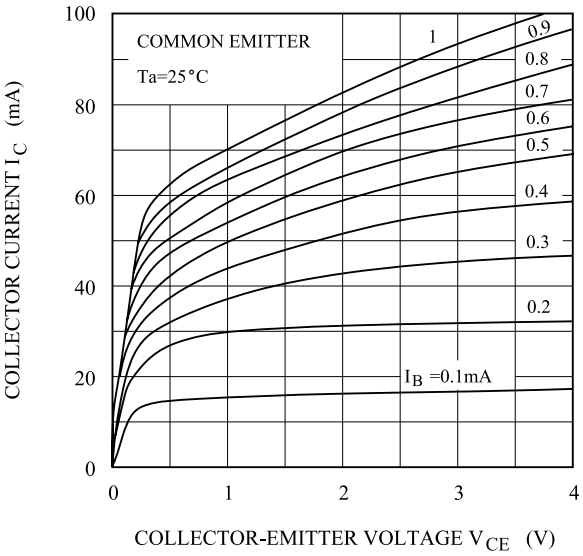


ELECTRICAL CHARACTERISTICS (Ta=25℃)

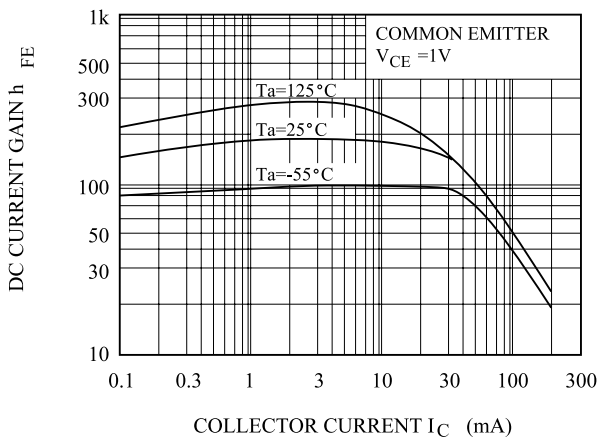
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CEX}	V_{CE}=30V, V_{EB}=3V	-	-	50	nA
Collector Cut-off Current		I_{CBO}	V_{CB}=30V, I_E=0	-	-	100	nA
Emitter Cut-off Current		I_{EBO}	V_{EB}=3V, I_C=0	-	-	100	nA
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$	I_C=10 μA, I_E=0	60	-	-	V
Collector-Emitter Breakdown Voltage *		$V_{(BR)CEO}$	I_C=1mA, I_B=0	40	-	-	V
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	I_E=10 μA, I_C=0	6.0	-	-	V
DC Current Gain *		h_{FE}	V_{CE}=1V, I_C=10mA	150	-	250	
Collector-Emitter Saturation Voltage *		$V_{CE(sat)}$	I_C=50mA, I_B=5mA	-	-	0.3	V
Base-Emitter Saturation Voltage *		$V_{BE(sat)}$	I_C=50mA, I_B=5mA	-	-	0.95	V
Transition Frequency		f_T	V_{CE}=20V, I_C=10mA, f=100MHz	250	-	-	MHz
Switching Time	Delay Time	t_d		-	-	35	nS
	Rise Time	t_r		-	-	35	
	Storage Time	t_{stg}		-	-	200	
	Fall Time	t_f		-	-	50	

* Pulse Test : Pulse Width≦300 μS, Duty Cycle≦2%.

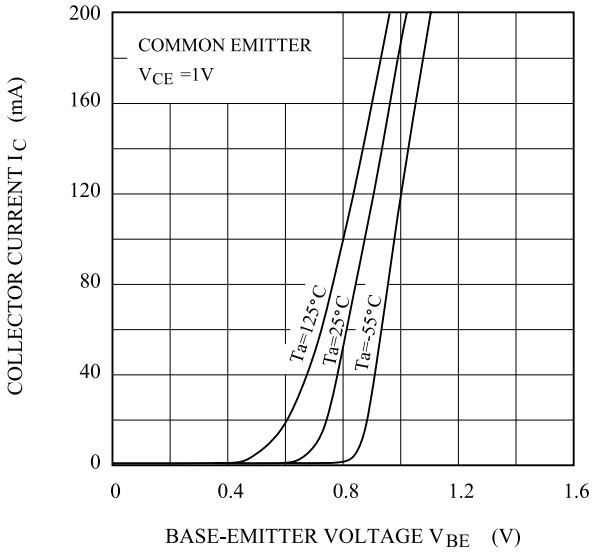
I_C - V_{CE}



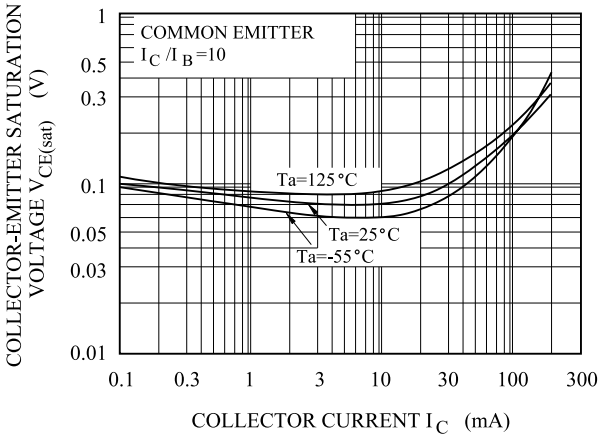
h_{FE} - I_C



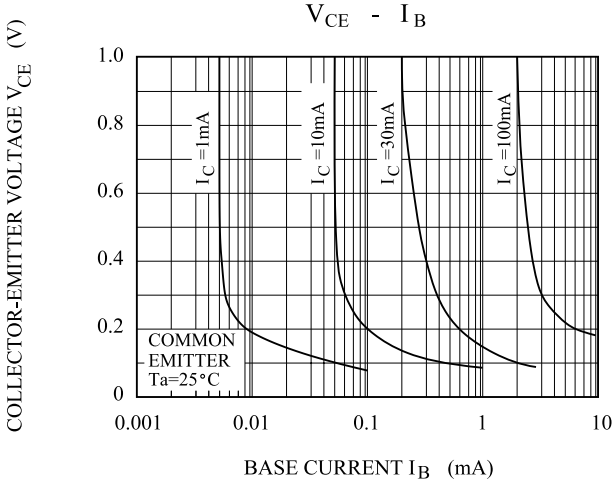
I_C - V_{BE}



$V_{CE(sat)}$ - I_C



V_{CE} - I_B



$V_{BE(sat)}$ - I_C